EAST Search History (10 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	("5,976,921").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:55
L2	3823	((257/173) or (257/174) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:56
L3	219	2 and (esd electrostatic adj discharge) and (bi$1directional$2 symmetric$2 symmetry reversible)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:01
L4	13	2 and (esd electrostatic adj discharge) and (bi$1directional$2 symmetric$2 symmetry reversible) and @ad<"19991111" and bias near4 (body substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:03
L5	16	((texas adj instrument$1).as. (robert near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi$1directional$2 symmetric$2 symmetry reversible) and @ad<"19991111" and bias near4 (body substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:07
L6	6	((texas adj instrument$1).as. (robert near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi$1directional$2 symmetric$2 symmetry reversible) and bias near4 (body substrate) and (bond adj pad external adj terminal).clm. and (transistor MOS MOSFET MISFET MIS).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:39
L7	2	"6784496".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:14

EAST Search History

L8	2	"6577481".pn.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:15
L9	2	"6624481".pn.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:15
L10	2	"6919603".pn.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:16
L11	2	"6940131".pn.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:19
L12	5	"926916".ap.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:21
L13	4	"690006".ap.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:22
L14	4	"690011".ap.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:23
L15	3	("9949800").PN.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:24
L16	2	("6949800").PN.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:24
L17	2	("6933741").PN.		US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:25

L18	2	("7060538").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:25
L19	2	("7034364").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
L20	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
L21	2	("6577481").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
L22	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:30
L23	2	("6940131").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:31
L24	2	("6424013").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:33
L25	2	("6628493").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:34
L26	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:35
L27	2	("6873506").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:36

EAST Search History

L28	2	("5850095").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:36
L29	2	("5808342").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:37
L30	2	("5747834").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
L31	2	("6016002").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
L32	2	("6174404").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
L33	2	("6172404").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 11:38
L34	2	((texas adj instrument$1).as. (robert near1 steinhoff).in. (jonathan near1 brodsky).in. (vrotsos near1 thomas).in.) and (esd electrostatic adj discharge) and (bi$1directional$2 symmetric$2 symmetry reversible) and (third adj (transistor mosfet mos misfet)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/06 11:40
S1	5	"498677".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/06 10:40
S2	32	(bidirectional bi-directional two-way comprehensive unified) near3 (electrostatic adj discharge esd).ti, ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 14:56

EAST Search History

S3	30	steinhoff.in. and esd	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:08
S4	2190	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:09
S5	166	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal and (bidirectional bi-directional "two way"$1 comprehensive unified)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:10
S6	53	(esd electrostatic adj discharge).ti, ab,clm. and transistor and terminal and (bidirectional bi-directional "two way"$1 comprehensive unified) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:22
S7	218	common near4 "source/drain" and gate near4 connect$3 near4 source and gate near4 connect$3 near4 drain	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25
S8	126	common near4 "source/drain" and gate near4 connect$3 near4 source and gate near4 connect$3 near4 drain and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/10 15:25
S9	2408	257/355	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S10	1058	257/356	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S11	1139364	"57"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S12	7749759	"8"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26

EAST Search History

S13	1179	257/360	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:26
S14	3567	((257/173) or (257/355) or (257/356) or (257/357) or (257/358) or (257/359) or (257/360)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:27
S15	16	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter invertor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:28
S16	17	S14 and protection adj circuit near10 ((cmos cmosfet) near4 (inverter invertor))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 15:58
S17	1822	(257/355).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 15:58
S18	207	S17 and inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:00
S19	103	S17 and inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:13
S20	365	esd adj protection adj circuit and integrated adj circuit and (CMOS CMOSFET invert?r) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 16:14
S21	454	esd adj protection adj circuit and integrated adj circuit and (BiCMOS CMOS CMOSFET invert?r) and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:08
S22	2	("6784496").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:13

S23	4	"407037".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:14
S24	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S25	2	("6919603").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:16
S26	2	("6577481").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:17
S27	0	("690006.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18
S28	0	("690011.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:18
S29	0	("6692606.ap.").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:19
S30	2	("6949800").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:19
S31	2	("6933741").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:20
S32	2	("7060538").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:21

S33	16	S22 S23 S24 S25 S26 S27 S28 S29 S30 S31 S32	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 17:23
S34	6	(US-7060538-$ or US-6949800-$ or US-6919603-$ or US-6784496-$ or US-6577481-$).did. or (US-6784496-$).did.	USPAT; DERWENT	OR	OFF	2006/09/19 17:25
S35	13	(bidirectional bi-directional) and ESD and biCMOS and SCR	USPAT; DERWENT	OR	ON	2006/09/19 17:53
S36	16	(bidirectional bi-directional) and ESD and biCMOS and SCR	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 17:56
S37	326	(257/358).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:23
S38	1	"6369427".pn. and substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29
S39	190	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/19 18:29
S40	198	esd adj protection and cmos adj inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:29
S41	123	esd adj protection and cmos adj inverter and @ad<"19991111"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/19 18:30
S42	2	"6369427".pn. and (ground terminal reference)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 08:57

EAST Search History

S43	1	"6369427".pn. and (substrate)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/09/20 09:04
S44	1	esd and inverter and (duf buried) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S45	0	esd and inverter and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S46	0	esd and (duf) and (semiconductor silicon) adj substrate and sinker	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S47	0	esd and (duf) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 09:17
S48	236	esd and (buried adj (layer region)) and (semiconductor silicon) adj substrate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:35
S49	100	esd and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
S50	58	esd.ti,ab,clm. and (buried adj (layer region)) and bipolar adj transistor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/09/20 10:36
S51	7	"498677".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 10:55
S52	2	"6369427".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 13:22

EAST Search History

S53	1636	ra adj value	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/06/05 11:15
S54	3	ra adj value.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/05 11:15
S55	4	"185411".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/05 13:23